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## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is characterized in that an angle  $\theta$  of inclination formed by the side surfaces of a ridge portion and a lower part of the ridge portion is at least  $70^\circ$  and not more than  $117^\circ$ , a p-type cladding layer is made of  $\text{Al}_{x_1}\text{Ga}_{1-x_1}\text{As}$ , a first current blocking layer is made of  $\text{Al}_{x_2}\text{Ga}_{1-x_2}\text{As}$ , the distance between an emission layer and the first current blocking layer satisfies the relation of  $t \leq 0.275/(1 - (x_2 - x_1))$  assuming that  $t$  represents the distance, and a lower width  $W$  of the ridge portion is at least  $2 \mu\text{m}$  and not more than  $5 \mu\text{m}$ .